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Application Number	09/997,997
Filing Date	November 30, 2001
First Named Inventor	Tomohiko SHIBATA
Art Unit	2834
Examiner Name	Not Assigned
Confirmation No.	3908
Attorney Docket No.	782 200

[illegible][illegible]

AA	S. Kaneko, et al, "Epitaxial Growth of AlN Film by Low-pressure MOCVD in Gas-Beam-Flow Reactor," Journal of Crystal Growth, 115 (1991), pp. 643-647.

Examiner:	<i>M. J. Quinn</i>	Date Considered:	40/15/03
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.